



DMNH10H028SPS

100V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI

Product Summary

V _{(BR)DSS}	Rds(on)	Ι _D T _C = +25°C
100V	28mΩ @ V _{GS} = 10V	40A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

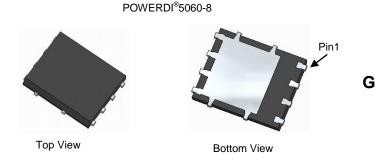
- Power Management Functions
- **DC-DC** Converters

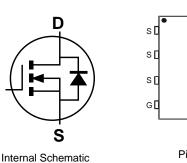
Features

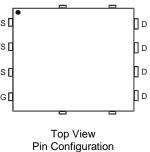
- Thermally Efficient Package-Cooler Running Applications
- **High Conversion Efficiency**
- Low R_{DS(ON)} Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile Ideal for Thin Applications
- Lead-Free Finish; RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMNH10H028SPSQ)

Mechanical Data

- Case: POWERDI[®]5060-8
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)







Ordering Information (Note 4)

Part Number	Case	Packaging
DMNH10H028SPS-13	POWERDI [®] 5060-8	2500 / Tape & Reel

1 of 7

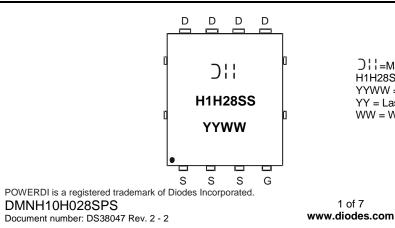
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied. Notes:

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



DII = Manufacturer's Marking H1H28SS = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 15 = 2015) WW = Week Code (01 to 53)



Maximum Ratings ($@T_C = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	100	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V	Ι _D	40 25	А		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) (Note 5)			I _{DM}	54	A
Maximum Continuous Body Diode Forward Current (Note 6)			ls	3.9	A
Avalanche Current (Note 8) L=0.1mH			I _{AS}	26	A
Avalanche Energy (Note 8) L=0.1mH			E _{AS}	35	mJ

Thermal Characteristics

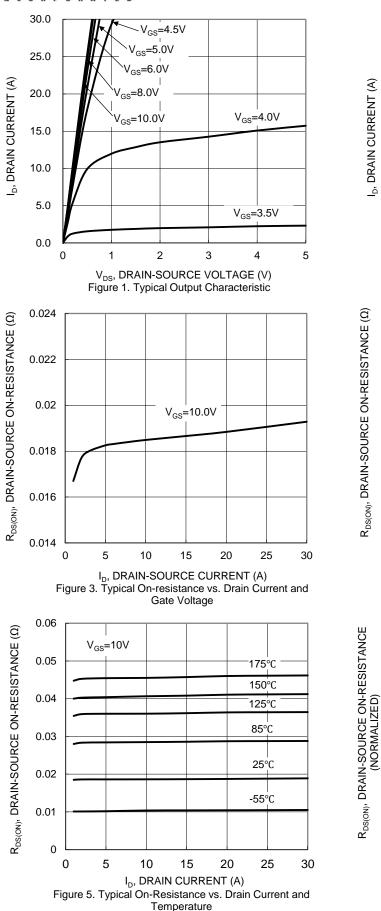
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	1.6	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	R _{θJA}	97	°C/W
Total Power Dissipation (Note 6)		PD	2.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	R _{θJA}	52	*CAM
Thermal Resistance, Junction to Case		R _{0JC}	1.8	°C/W
Operating and Storage Temperature Range		T _{J.} T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_C = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Turn	Max	110:4	Test Condition
	Symbol	IVIIN	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)		100	1	1		
Drain-Source Breakdown Voltage	BV _{DSS}	100		—	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	IDSS	—	—	1.0	μA	$V_{DS} = 100V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	2.0	2.5	4.0	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$
Static Drain-Source On-Resistance	R _{DS(ON)}		19	28	mΩ	$V_{GS} = 10V, I_D = 20A$
Diode Forward Voltage	V _{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1.0A$
DYNAMIC CHARACTERISTICS (Note 8)			•			
Input Capacitance	Ciss	_	2245	_		$V_{DS} = 50V, V_{GS} = 0V$ f = 1.0MHz
Output Capacitance	Coss	_	173	—	pF	
Reverse Transfer Capacitance	C _{rss}	_	68	_		
Gate Resistance	R _G	_	1.9	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V _{GS} = 10V)	Qg	_	36	—		$V_{DD} = 50V, I_D = 20A$
Total Gate Charge ($V_{GS} = 6.0V$)	Qg	-	22	_	nC	
Gate-Source Charge	Q _{gs}	_	7.3	_	10	
Gate-Drain Charge	Q _{gd}	_	9.2	_		
Turn-On Delay Time	t _{D(ON)}	_	6.4	—		$V_{GS} = 10V, V_{DS} = 50V,$ $R_G = 3.0\Omega, I_D = 20A$
Turn-On Rise Time	t _R	_	5.8	_		
Turn-Off Delay Time	t _{D(OFF)}	_	17.8	_	ns	
Turn-Off Fall Time	tF	_	4.8	_]	
Reverse Recovery Time	t _{RR}	_	35	_	ns	I _F = 20A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{RR}	_	47	_	nC	I _F = 20A, di/dt = 100A/µs

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing. Notes:





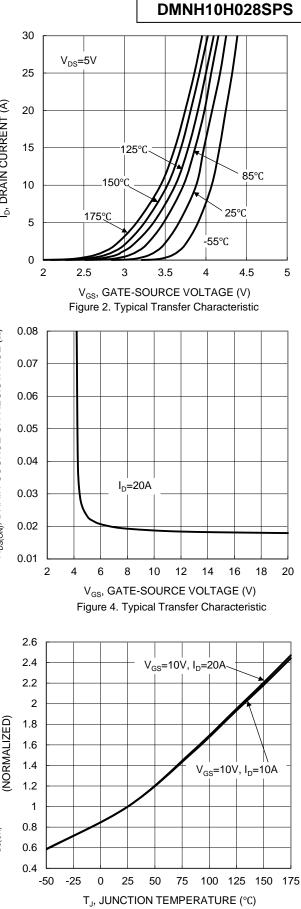
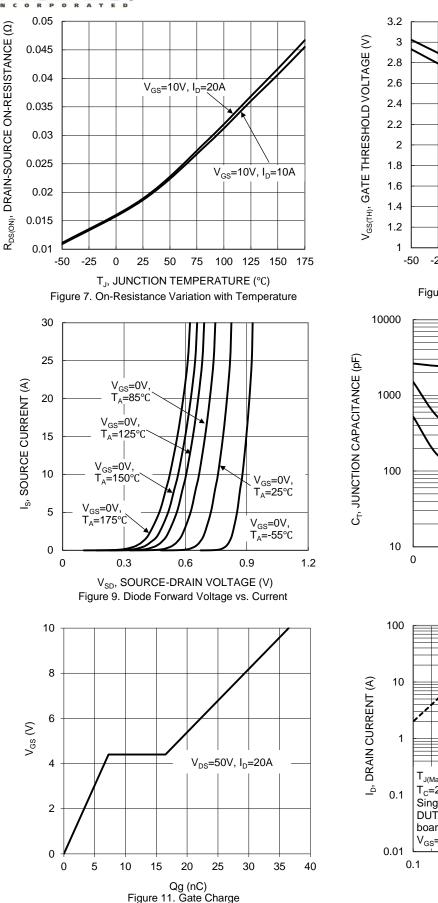
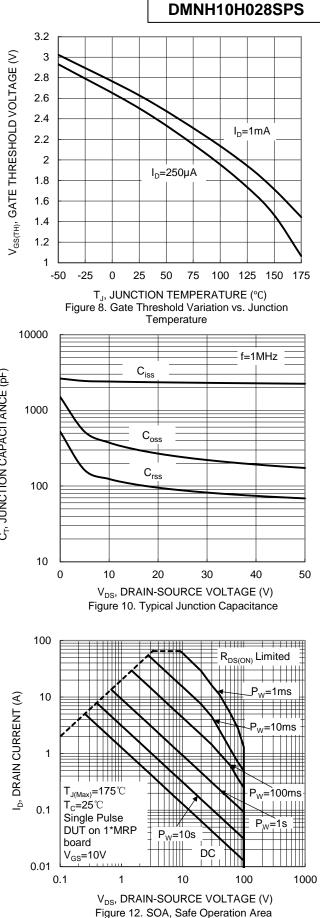


Figure 6. On-Resistance Variation with Temperature



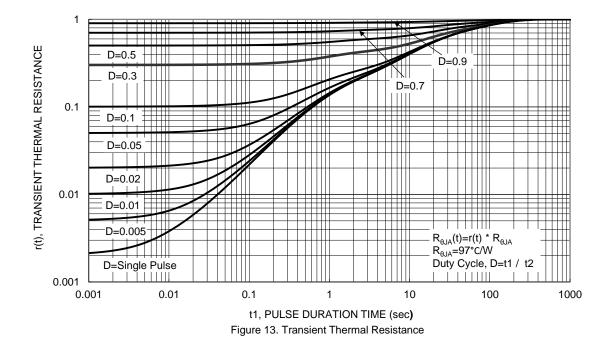




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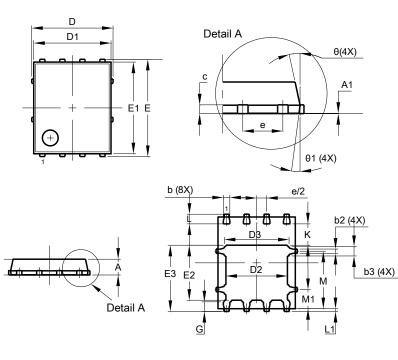






Package Outline Dimensions

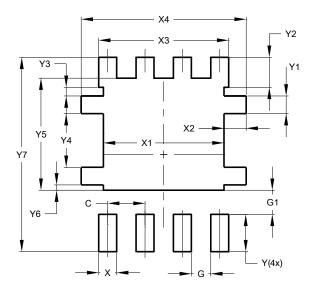
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



		(R) = 0 = 0					
	POWERDI [®] 5060-8						
Dim	Min	Max	Тур				
Α	0.90	1.10	1.00				
A1	0.00	0.05					
b	0.33	0.51	0.41				
b2	0.200	0.350	0.273				
b3	0.40	0.80	0.60				
C	0.230	0.330	0.277				
D		5.15 BSC	;				
D1	4.70	5.10	4.90				
D2	3.70	4.10	3.90				
D3	3.90	4.30	4.10				
E		6.15 BSC					
E1	5.60	6.00	5.80				
E2	3.28	3.68	3.48				
E3	3.99	4.39	4.19				
е		1.27 BSC					
G	0.51	0.71	0.61				
K	0.51						
L	0.51	0.71	0.61				
L1	0.100	0.200	0.175				
М	3.235	4.035	3.635				
M1	1.00	1.40	1.21				
Θ	10º	12º	11º				
Θ1	6°	8º	7°				
AI	All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

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